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(3) s

Schematic diagram

NCEP85T16 XXXX

Marking and pin assignment

TO-220-3L top view

NCE

(1) G C

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP85T16 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =85V,I_D =160A
 R_{DS(ON)} <3.8mΩ @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T16	NCEP85T16	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	85	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι _D	160	А	
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	112	А	
Pulsed Drain Current	I _{DM}	480	А	
Maximum Power Dissipation	PD	220	W	
Derating factor		1.5	W/℃	
Single pulse avalanche energy ^(Note 5)	E _{AS}	1440	mJ	
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C	







Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{ejc}	0.6	°C /W
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Electrical Characteristics (T_C=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =85V, V_{GS} =0V	_{DS} =85V,V _{GS} =0V -		1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·····		•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, I _D =250µA	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =80A	-	3.1	3.8	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =80A	75	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	8500	-	PF
Output Capacitance	C _{oss}	V_{DS} =40V, V_{GS} =0V,	-	1520	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	81	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	30.5	-	nS
Turn-on Rise Time	tr	V _{DD} =40V,I _D =80A	-	29	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =4.7 Ω	-	95	-	nS
Turn-Off Fall Time	t _f		-	34.5	-	nS
Total Gate Charge	Qg	N/ 40\/ L 00.4	-	105		nC
Gate-Source Charge	Q _{gs}	V_{DS} =40V,I _D =80A,	-	39		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	28		nC
Drain-Source Diode Characteristics					•	•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =160A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	160	Α
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	95		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	225		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t \leq 10 sec.

3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ C$,V_{DD}=42.5V,V_G=10V,L=0.5mH,Rg=25\Omega

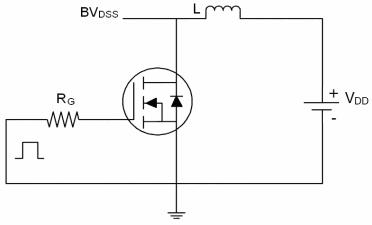


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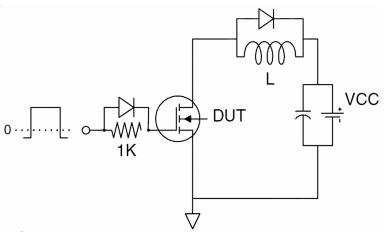




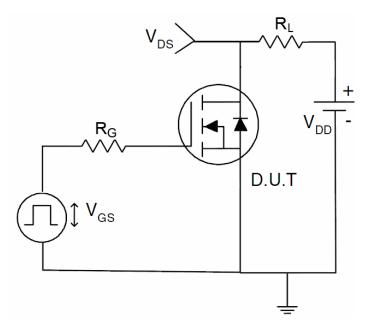
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





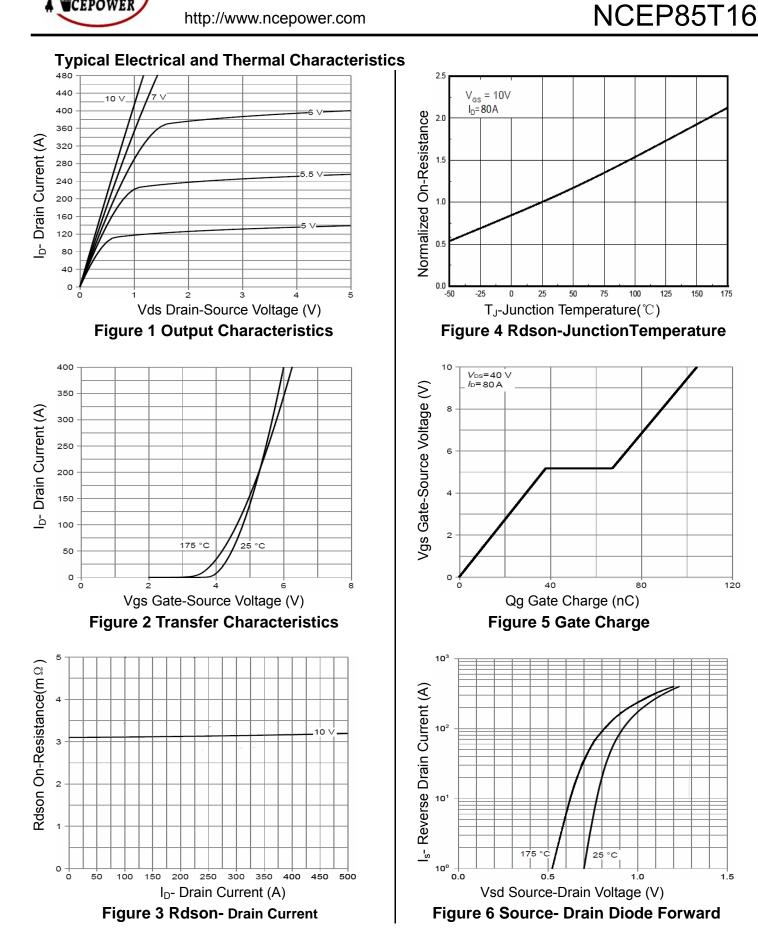
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175

120





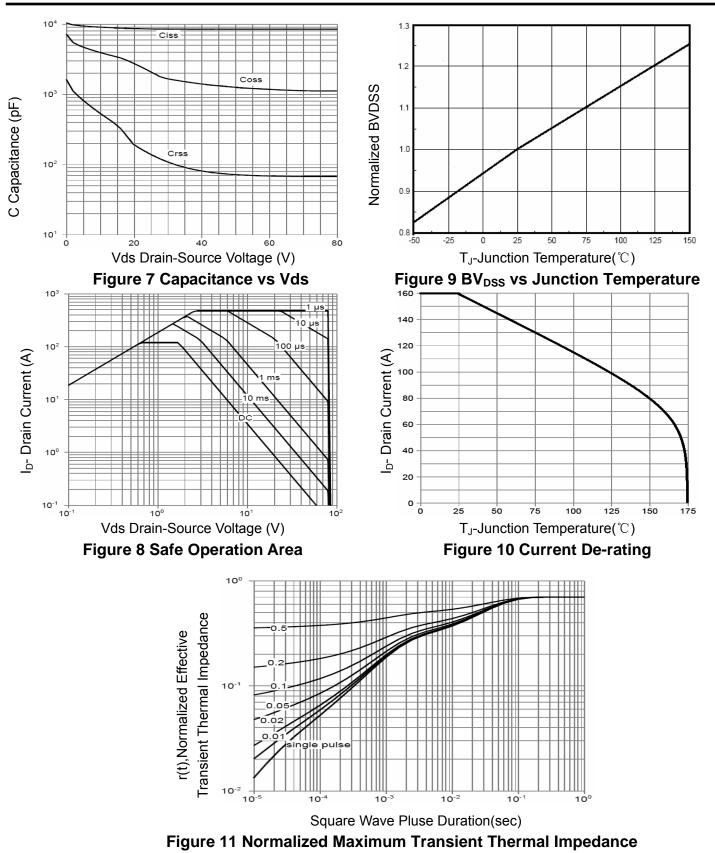
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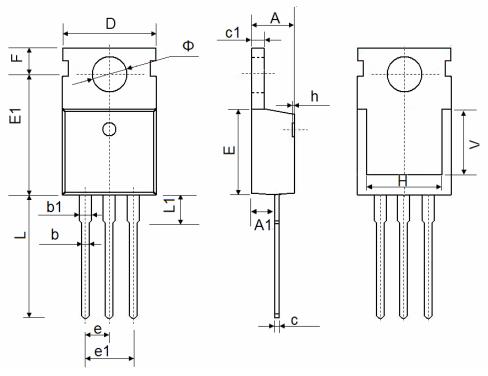


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TO-220-3L Package Information



Cumhal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	2.540 TYP. 0.100 TYP.		TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	







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